Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2.4	C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	100	C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	C

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I_D =-250uA	-60			V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} =V_{DS}, I_D =-250uA	-1.2		-2.5	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=-60V, V_{GS} =0V			1.0	uA
Gate- Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS} =0V			100	nA
Static Drain-source On Resistance	0 $_{1}$ -	V_{GS}=-10V, I_D				

Fig.1 Gate-Charge Characteristics

Fig.2 Capacitance Characteristics

Fig.3 Power Dissipation Derating Curve

Fig.

- 0 A 41 1 A 4

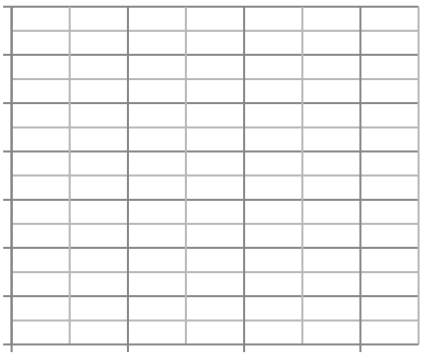

Fig.9 SOA Maximum Safe Operating Area

- 0 A 4 1 (A

Fig.10 ID-Junction Temperature

Fig.11 Switching Time Measurement Circuit

Fig.12 Gate Charge Waveform

Fig.8 Gate Charge Waveform

Fig.13 Switching Time Measurement Circuit

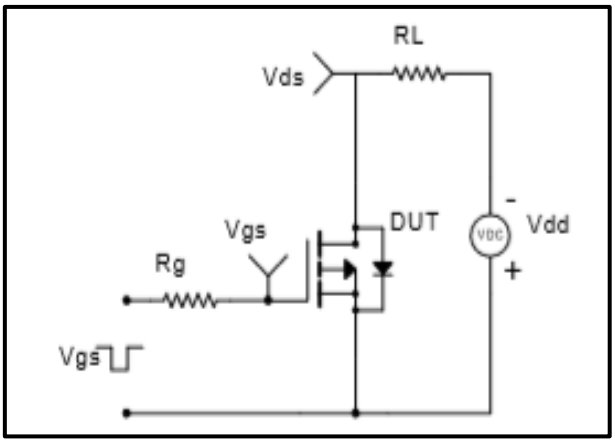

Fig.14 Gate Charge Waveform

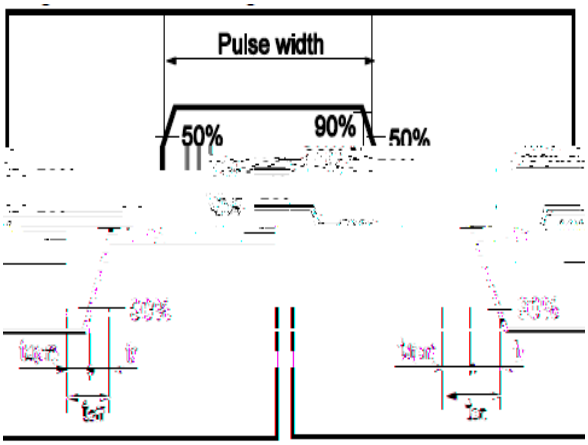

Fig.15 Avalanche Measurement Circuit

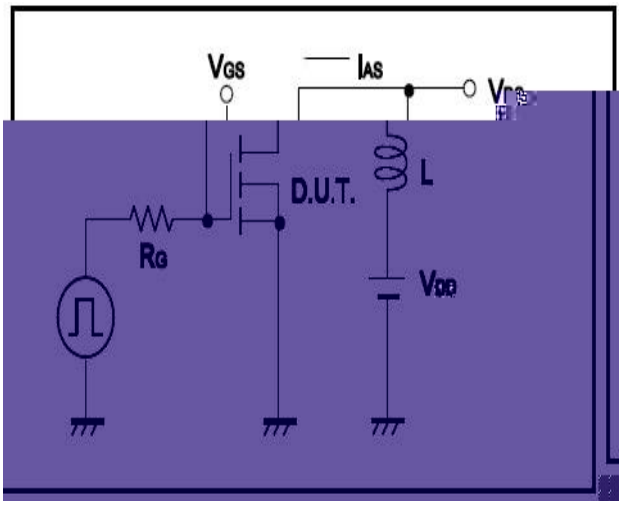

Fig.16 Avalanche Waveform